Supporting Information:

Solution-processed PSS:MoO$_x$ composite thin film with triple-function: passivation, antireflection and hole-selective transport for application into IBC solar cells

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Keywords: crystalline silicon; passivation; surface engineering; functional group; the sulfonic functional group

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Figure 1 XRD graphic of MoO$_x$ thin film

Figure S2 Typical He I (hv= 21.22 eV) UPS spectrum of MoO$_x$ (250 nm) thin film taken with 30.0 V bias applied to the sample
Figure S3 The mixed PSS:MoO$_x$ solutions with different molar ratios (the molar ratio of PSS to MoO$_x$ (1:x), where x is equal to 0.5, 10, 30, 50)

Figure S4 The AFM surface morphologies of MoO$_x$ thin film on Si substrate with RMS of 9.39 nm